

Over-voltage Protection Thyristor

Description

DO-214AC P Series solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

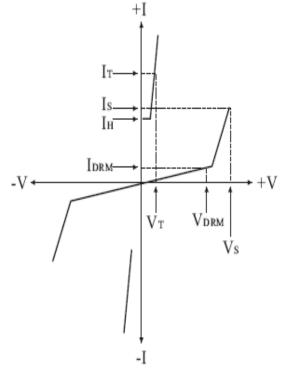
P Series devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

Compared to surge suppression using other technologies, P Series devices offer absolute surge protection regardless of the surge current available and the rate of applied voltage (dv/dt). P Series devices:

- Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigu
- Have low capacitance, making them ideal for high-speed transmission equipment

Electrical Parameters

arameter	Definition
C 0	Off-state Capacitance — typical capacitance
	measured in off state
di/dt	Rate of Rise of Current — maximum rated value of
	the acceptable rate of rise in current over time
Is	Switching Current — maximum current required to
	switch to on state
I DRM	Leakage Current — maximum peak off-state current
	measured at VDRM
\mathbf{I}^{H}	Holding Current — minimum current required to
	maintain on state
I PP	Peak Pulse Current — maximum rated peak impulse
	current
IT	On-state Current — maximum rated continuous
	on-state current
I TSM	Peak One-cycle Surge Current — maximum rated
	one-cycle AC current
VS	Switching Voltage — maximum voltage prior to
	switching to on state
V DRM	Peak Off-state Voltage — maximum voltage that can
	be applied while maintaining off state
VF	On-state Forward Voltage — maximum forward
	voltage measured at rated on-state current
VT	On-state Voltage — maximum voltage measured at
	rated on-state current





SP1300TA

P Series

ROHS

Senchip

P Series

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Vdrm	Vs	VT	Idrm	Is	Ιτ	Ін	Co		
Volts	Volts	Volts	μ Amps	mAmps	Amps	mAmps	pF		
120	160	4	5	800	2.2	150	35		
	VDRM Volts	VDRM Vs Volts Volts	VDRM Vs VT Volts Volts Volts	VDRM Vs VT IDRM Volts Volts Volts µAmps	vracteristics VDRM Vs Vr IDRM Is Volts Volts Volts µAmps mAmps	vracteristics VDRM Vs Vr IDRM Is Ir Volts Volts Volts µAmps mAmps Amps	Protection Thyristor SP1300TA uracteristics VDRM Vs Vr IDRM Is Ir IH VOIts Volts Volts µ Amps mAmps Amps mAmps		

* For surge ratings, see table below.

Notes:

• All measurements are made at an ambient temperature of 25°C. IPP applies to -40°C through +85°C temperature range.

• Off-state capacitance (Co) is measured at 1 MHz with a 2 V bias and is typical value.

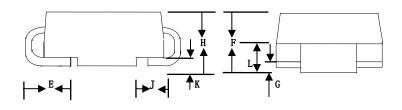
Surge Rati	ings						
Series	Ipp 2/10 μs Amps	Ipp 8/20 μs Amps	IPP 10/160 µs Amps	IPP 10/560 µs Amps	IPP 10/1000 μs Amps	Itsm 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
Thermal Co	onsiderations						
Package	DO-214AC/SMA	Symbol	Parameter			Value	Unit
	•	T_{J}	Operatin	ng Junction Te	mperature	-40 to +1	150 °C
		Ts	Storage Temperature Range Junction to Ambient on printed circuit			-40 to +1	150 °C
		$R_{\theta JA}$				120	°C/W

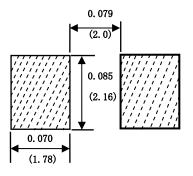


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SP1300TA

Dimensions





SMA

Dimension	Inc	ches	Millimeters		
	MIN	MAX	MIN	MAX	
A	0.098	0.114	2.50	2.90	
В	0.188	0.208	4.80	5.28	
С	0.055	0.062	1.40	1.60	
D	0.157	0.181	4.00	4.60	
Е	0.030	0.060	0.76	1.52	
F	0.078	0.096	2.00	2.44	
Н	0.080	0.104	2.051	2.643	
J	0.043	0.053	1.09	1.35	
K	0.008	0.014	0.20	0.35	
L	0.039	0.049	0.99	1.24	

P Series

ROHS



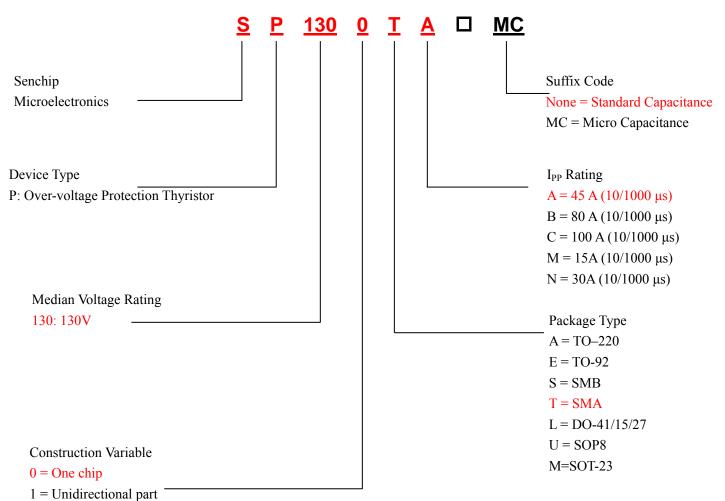
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Description of Part Number



2 =Two chips

3 = Three chips

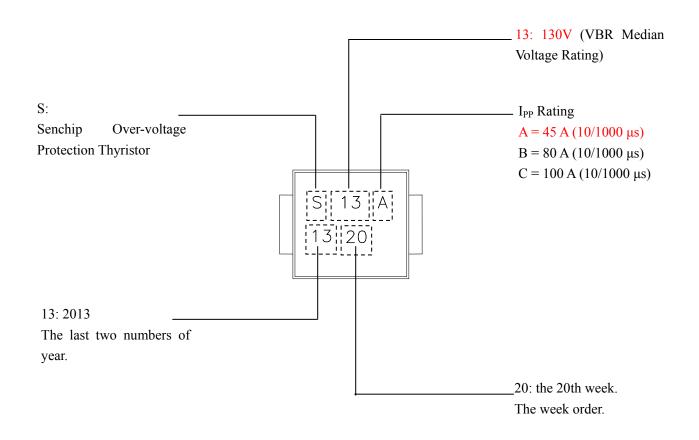


P Series

ROHS

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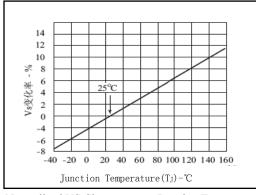
Description of Marking





Senchip			P Series
Over-voltage Protec	tion Thyristor	SP1300TA	ROHS
Summary of Packing	Options		
Package Type	Description	Packing Quantity	Industry Standard
DO-214AC TA	Embossed Carrier Reel Pack	5000 PCS	EIA RS-481

Thermal Derating Curves



Normalized VS Change versus Junction Temperature

